

MOSFET – Power, Single N-Channel

40 V, 3.3 mΩ, 157 A

NVMJST3D3N04C

Features

- Small Footprint (5x7 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- TCPAK57 5x7 Top Cool Package
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	40	V	
Gate-to-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)	Steady State	$T_C = 25^\circ\text{C}$	I_D 157	A
		$T_C = 100^\circ\text{C}$	111	
Power Dissipation $R_{\theta JC}$ (Note 1)		$T_C = 25^\circ\text{C}$	P_D 150	W
		$T_C = 100^\circ\text{C}$	75	
Pulsed Drain Current	$T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$	I_{DM} 900	A	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)	I_S	125	A	
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 7.0 \text{ A}$)	E_{AS}	215	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260	$^\circ\text{C}$	

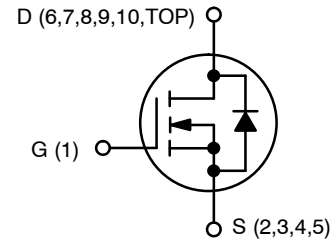
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

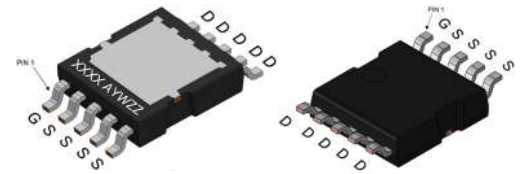
Parameter	Symbol	Value	Unit
Junction-to-Heatsink Top – Steady State (Note 2)	ψ_{JH}	3.1	$^\circ\text{C}/\text{W}$
Junction-to-Drain	ψ_{JL}	7.1	$^\circ\text{C}/\text{W}$
Junction-to-Source Lead	ψ_{JL}	6.8	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	31.1	$^\circ\text{C}/\text{W}$
Junction-to-Case – Steady State	$R_{\theta JC}$	1	$^\circ\text{C}/\text{W}$

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. 2s2p JEDEC51-7 standard PCB mounted to a 25x25x3 (mm) aluminum heatsink with a 12 w/mK TIM interface
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	3.3 mΩ @ 10 V	157 A

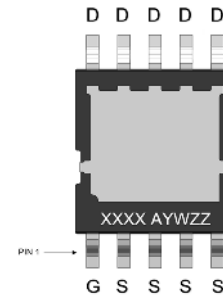


N-CHANNEL MOSFET



TCPAK57
CASE 760AG

MARKING DIAGRAM



XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			22		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}$	$T_J = 25^\circ\text{C}$		10	μA
			$T_J = 125^\circ\text{C}$		100	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 60\ \mu\text{A}$	2.5		3.5	V
Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			-7.8		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 50\text{ A}$		2.8	3.3	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 50\text{ A}$		93		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 25\text{ V}$		1600		μF
Output Capacitance	C_{OSS}			830		
Reverse Transfer Capacitance	C_{RSS}			28		
Total Gate Charge	$Q_G(TOT)$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}; I_D = 50\text{ A}$		23		nC
Threshold Gate Charge	$Q_G(TH)$			5.1		
Gate-to-Source Charge	Q_{GS}			9.0		
Gate-to-Drain Charge	Q_{GD}			3.5		
Plateau Voltage	V_{GP}			5.3		

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 20\text{ V}, I_D = 50\text{ A}, R_G = 2.5\ \Omega$		10		ns
Rise Time	t_r			47		
Turn-Off Delay Time	$t_{d(OFF)}$			19		
Fall Time	t_f			3.0		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 50\text{ A}$	$T_J = 25^\circ\text{C}$		0.9	1.2	V
			$T_J = 125^\circ\text{C}$		0.78		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 50\text{ A}$		37		ns	
Charge Time	t_a			18			
Discharge Time	t_b			19			
Reverse Recovery Charge	Q_{RR}			23			nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

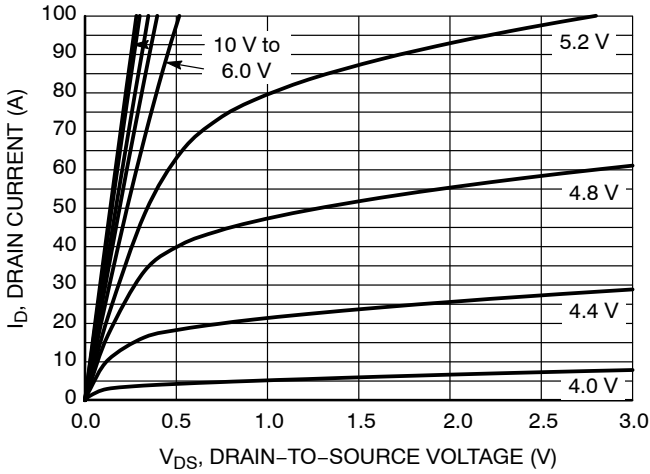


Figure 1. On-Region Characteristics

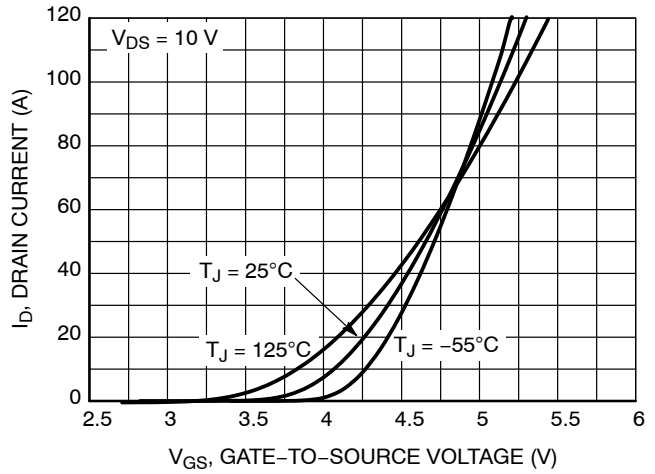


Figure 2. Transfer Characteristics

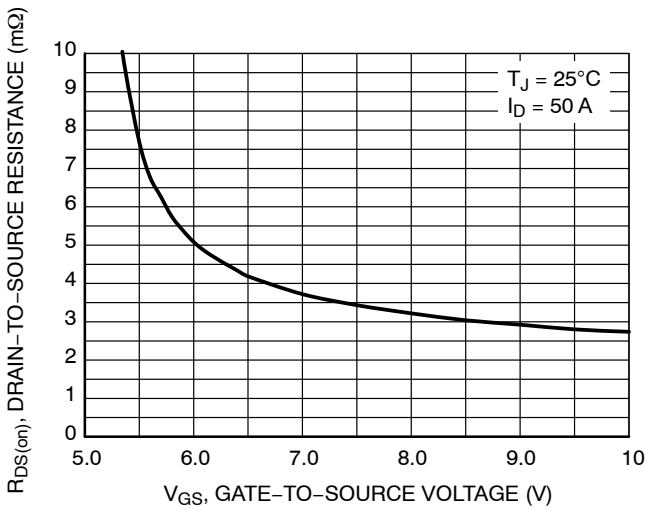


Figure 3. On-Resistance vs. Gate-to-Source Voltage

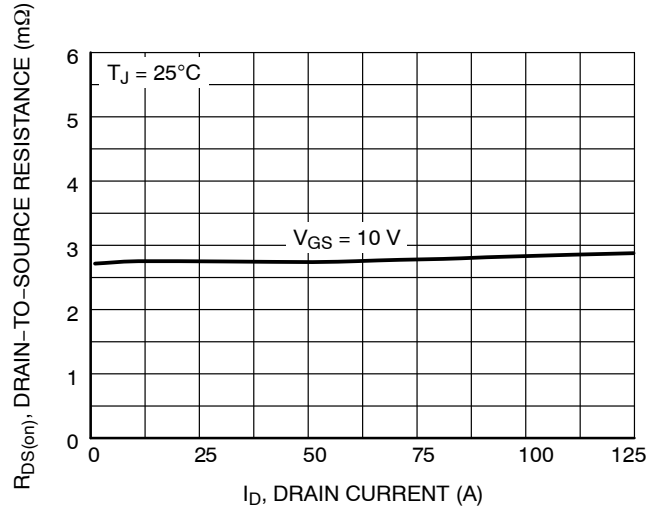


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

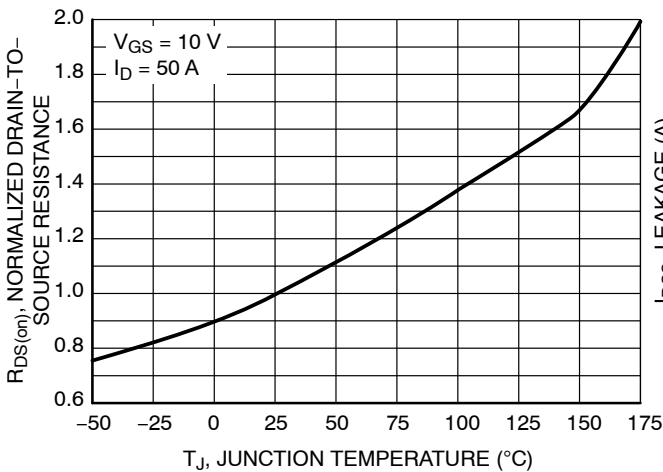


Figure 5. On-Resistance Variation with Temperature

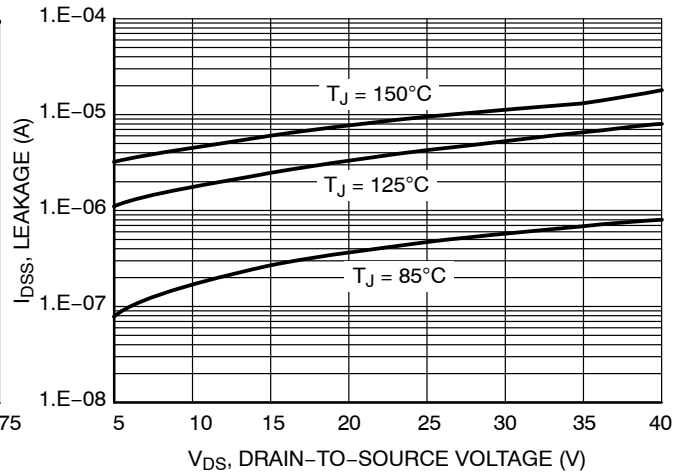


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS

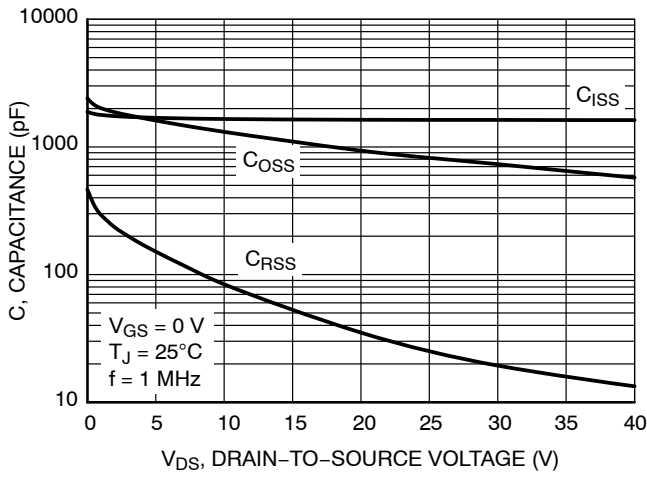


Figure 7. Capacitance Variation

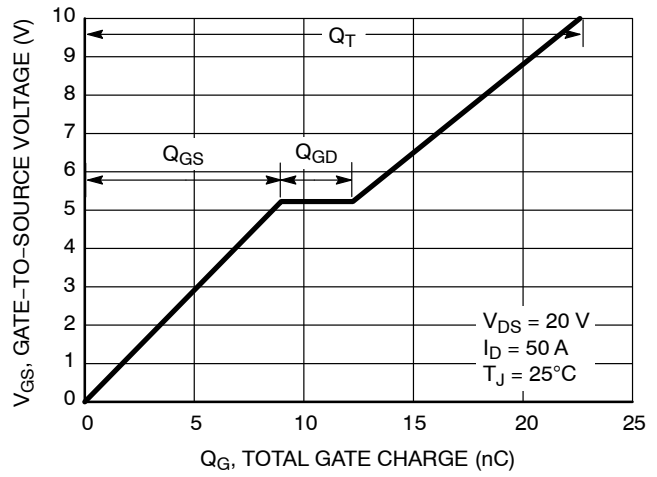


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

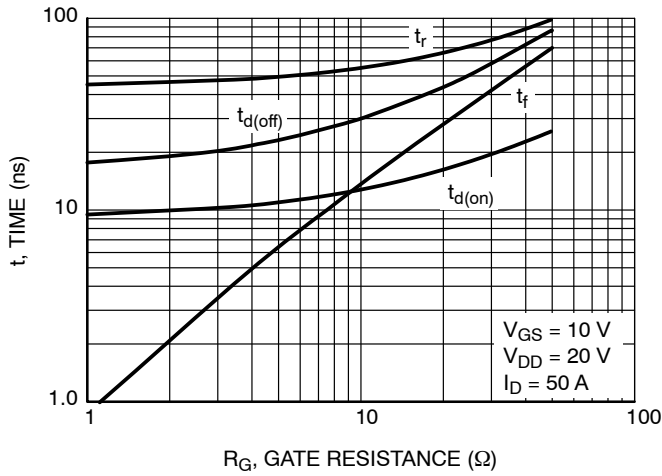


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

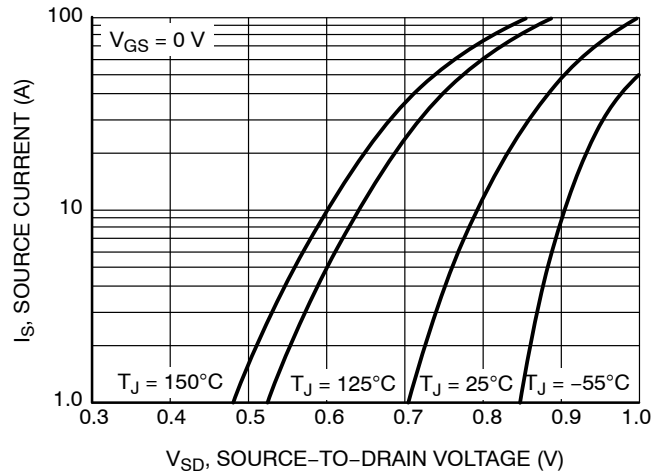


Figure 10. Diode Forward Voltage vs. Current

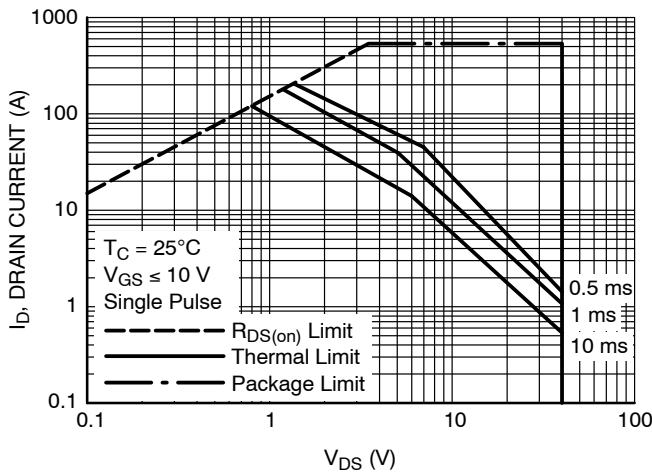


Figure 11. Safe Operating Area

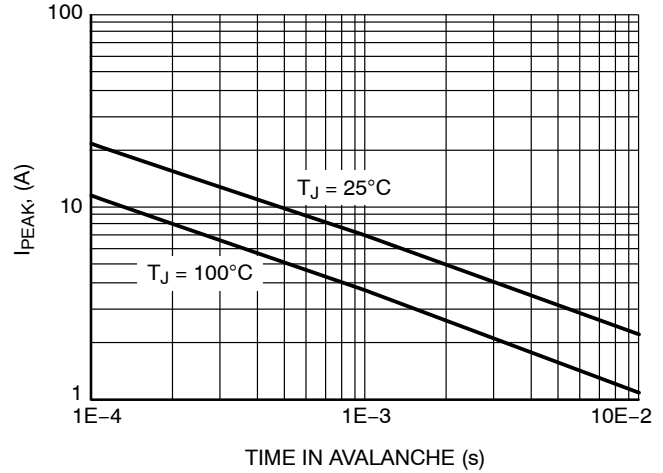


Figure 12. I_{PEAK} vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

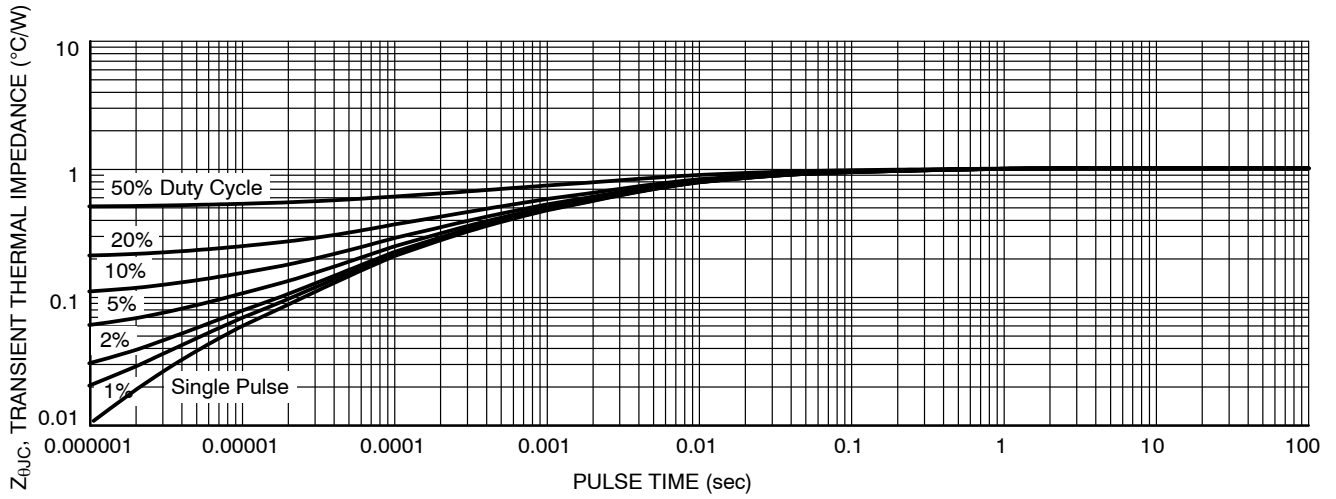


Figure 13. Thermal Characteristics

DEVICE ORDERING INFORMATION

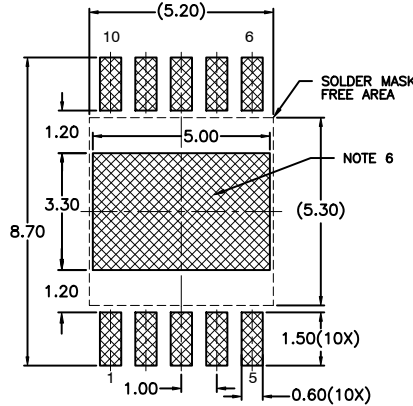
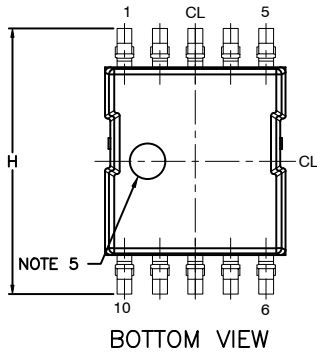
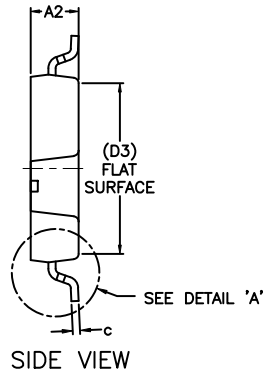
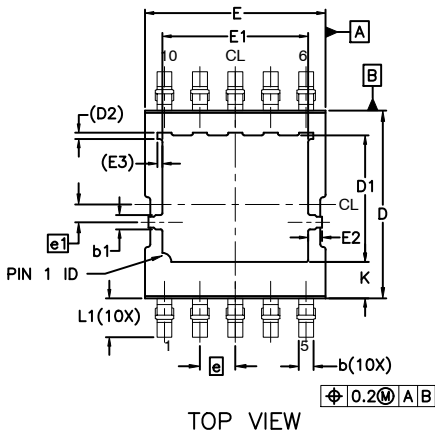
Device	Marking	Package	Shipping [†]
NVMJST3D3N04CTXG	3D34C	TCPAK57 Top Cool (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

TCPAK57 7.5x5
CASE 760AG
ISSUE B



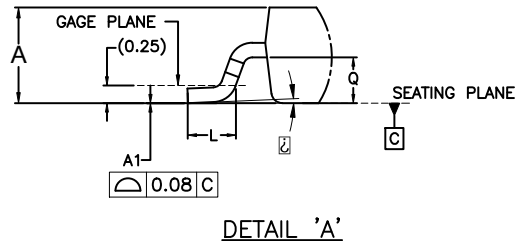
LAND PAD RECOMMENDATION

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. UNIT DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. OPTIONAL MOLD FEATURE.
6. LAND PAD UNDER THE PACKAGE BODY IS FOR MECHANICAL SUPPORT ONLY. SOLDER CONNECTION IS NOT REQUIRED.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	1.30	1.35	1.45
A1	-0.05	0.00	0.05
A2	1.30	1.35	1.40
b	0.36	0.41	0.46
b1	0.30	0.40	0.50
c	0.16	0.21	0.26
D	5.20	5.30	5.40
D1	3.47	3.57	3.67
D2	0.17 REF		
D3	4.82 REF		
E	5.00	5.10	5.20
E1	4.02	4.12	4.22
E2	0.30	0.40	0.50
E3	0.14 REF		
e	1.00 BSC		
e1	0.50 BSC		
K	0.93	1.03	1.13
H	7.30	7.50	7.70
L	0.49	0.69	0.89
L1	0.90	1.10	1.30
Q	0.60	0.65	0.70
⌀	0°	2.5°	5°



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For additional information, please contact your local Sales Representative

